



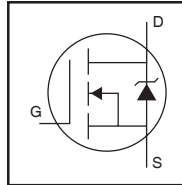
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AUTOMOTIVE GRADE

AUIRFR4105Z
AUIRFU4105Z

Features

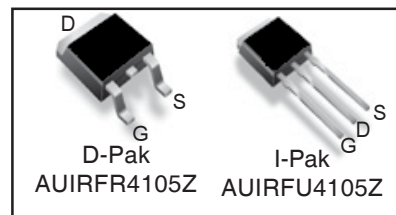
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



| | |
|-------------------|---------------|
| $V_{(BR)DSS}$ | 55V |
| $R_{DS(on)}$ max. | 24.5mΩ |
| I_D | 30A |

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

| | Parameter | Max. | Units |
|---------------------------|--|--------------------------|--------------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 30 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 21 | |
| I_{DM} | Pulsed Drain Current ① | 120 | |
| $P_D @ T_C = 25^\circ C$ | Power Dissipation | 48 | W |
| | Linear Derating Factor | 0.32 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ② | 29 | mJ |
| $E_{AS} (tested)$ | Single Pulse Avalanche Energy Tested Value ③ | 46 | |
| I_{AR} | Avalanche Current ① | See Fig.12a, 12b, 15, 16 | A |
| E_{AR} | Repetitive Avalanche Energy ③ | | mJ |
| T_J | Operating Junction and | -55 to + 175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds (1.6mm from case) | 300 | |
| | Mounting Torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|-----------------------------------|-------------|-------------|--------------|
| $R_{\theta JC}$ | Junction-to-Case ④ | — | 3.12 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount) ⑤ | — | 50 | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 110 | |



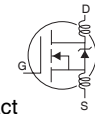
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| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--------------------------------------|------|-------|------|-------|--|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 55 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.053 | — | V/°C | Reference to 25°C, $I_D = 1mA$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | 19 | 24.5 | mΩ | $V_{GS} = 10V, I_D = 18A$ ③ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 2.0 | — | 4.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| g_{fs} | Forward Transconductance | 16 | — | — | S | $V_{DS} = 15V, I_D = 18A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | $V_{DS} = 55V, V_{GS} = 0V$ |
| | | — | — | 250 | | $V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ C$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 200 | nA | $V_{GS} = 20V$ |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | $V_{GS} = -20V$ |

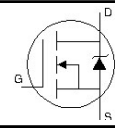
Dynamic Electrical Characteristics @ $T_J = 25^\circ C$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------------|---------------------------------|------|------|------|-------|---|
| Q_g | Total Gate Charge | — | 18 | 27 | nC | $I_D = 18A$ $V_{DS} = 44V$ $V_{GS} = 10V$ ③ |
| Q_{gs} | Gate-to-Source Charge | — | 5.3 | — | | |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | 7.0 | — | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 10 | — | ns | $V_{DD} = 28V$ $I_D = 18A$ $R_G = 24.5 \Omega$ $V_{GS} = 10V$ ③ |
| t_r | Rise Time | — | 40 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 26 | — | | |
| t_f | Fall Time | — | 24 | — | | |
| L_D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 7.5 | — | | |
| C_{iss} | Input Capacitance | — | 740 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 140 | — | | $V_{DS} = 25V$ |
| C_{rss} | Reverse Transfer Capacitance | — | 74 | — | | $f = 1.0MHz$ |
| C_{oss} | Output Capacitance | — | 450 | — | | $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$ |
| C_{oss} | Output Capacitance | — | 110 | — | | $V_{GS} = 0V, V_{DS} = 44V, f = 1.0MHz$ |
| $C_{oss \text{ eff.}}$ | Effective Output Capacitance | — | 180 | — | | $V_{GS} = 0V, V_{DS} = 0V \text{ to } 44V$ ④ |



Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|---|------|------|-------|---|
| I_S | Continuous Source Current (Body Diode) | — | — | 30 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | 120 | | |
| V_{SD} | Diode Forward Voltage | — | — | 1.3 | V | $T_J = 25^\circ C, I_S = 18A, V_{GS} = 0V$ ③ |
| t_{rr} | Reverse Recovery Time | — | 19 | 29 | ns | $T_J = 25^\circ C, I_F = 18A, V_{DD} = 28V$ |
| Q_{rr} | Reverse Recovery Charge | — | 14 | 21 | nC | $di/dt = 100A/\mu s$ ③ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D) | | | | |





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| | | | |
|-----------------------------------|----------------------|---|------|
| Qualification Level | | Automotive (per AEC-Q101) ^{††} | |
| | | Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | D-PAK | MSL1 |
| | | I-PAK | MSL1 |
| ESD | Machine Model | Class M2 (200V) AEC-Q101-002 | |
| | Human Body Model | Class H1A (500V) AEC-Q101-001 | |
| | Charged Device Model | Class C5 (1125V) AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

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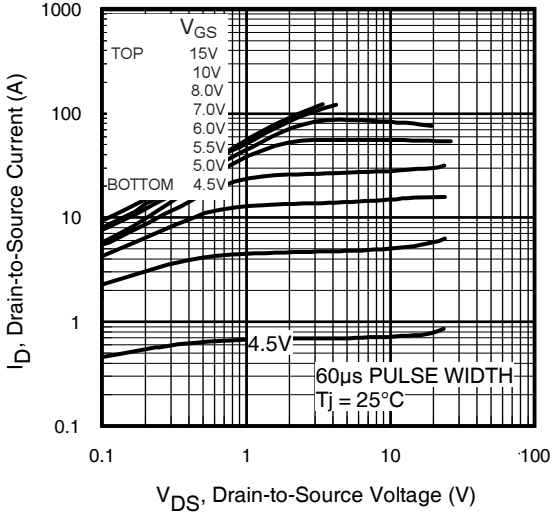


Fig 1. Typical Output Characteristics

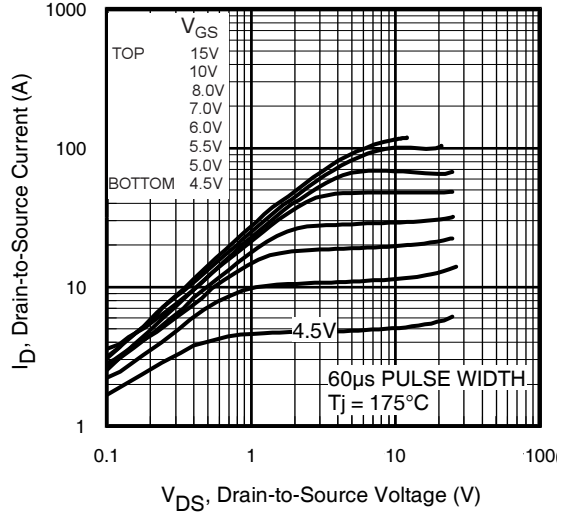


Fig 2. Typical Output Characteristics

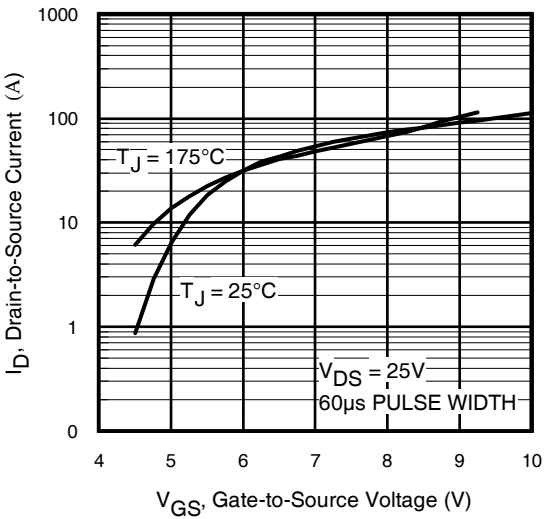


Fig 3. Typical Transfer Characteristics

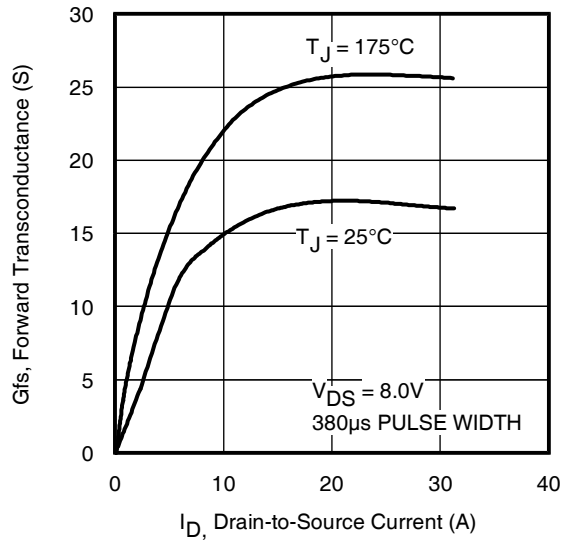


Fig 4. Typical Forward Transconductance Vs. Drain Current

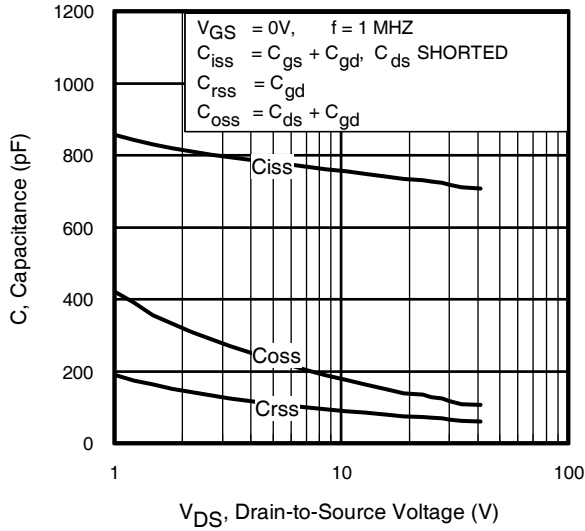


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

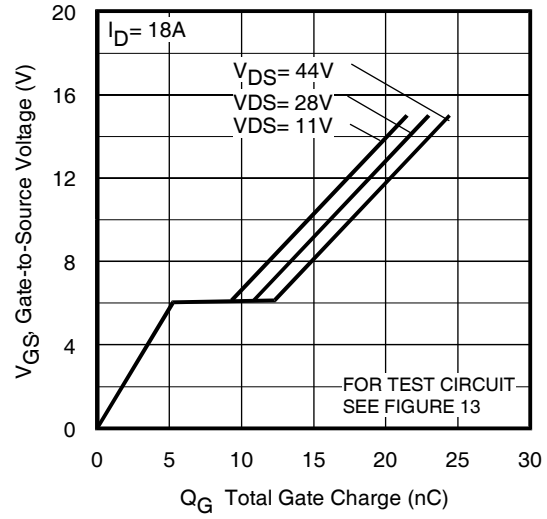


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

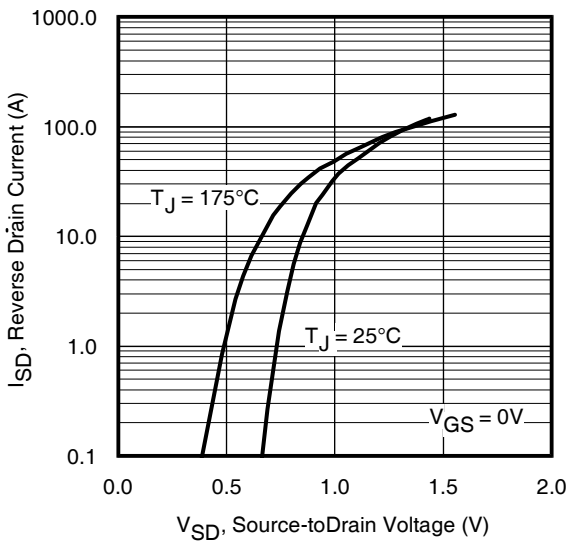


Fig 7. Typical Source-Drain Diode Forward Voltage

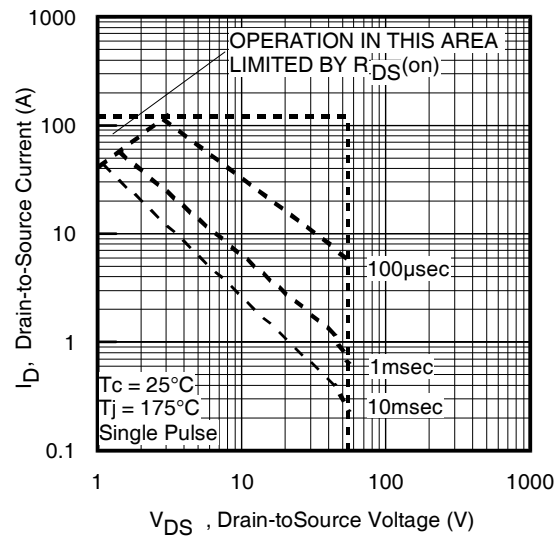


Fig 8. Maximum Safe Operating Area

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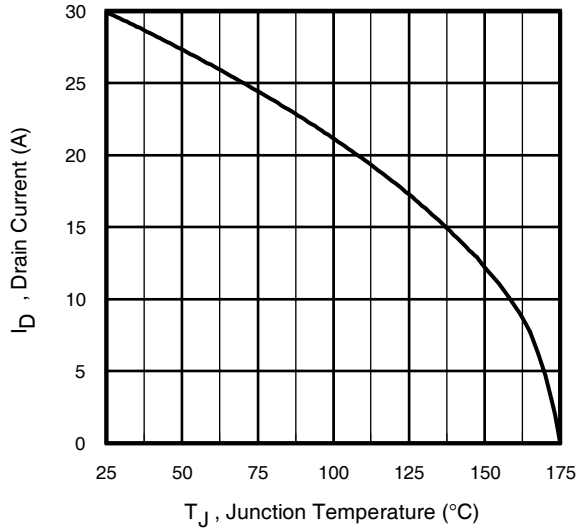


Fig 9. Maximum Drain Current Vs. Case Temperature

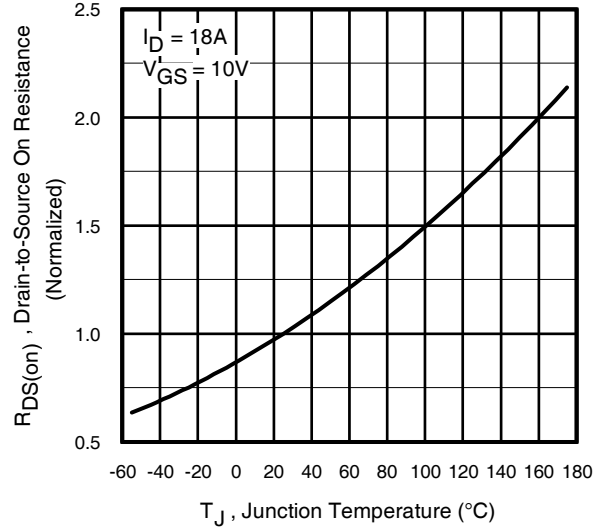


Fig 10. Normalized On-Resistance Vs. Temperature

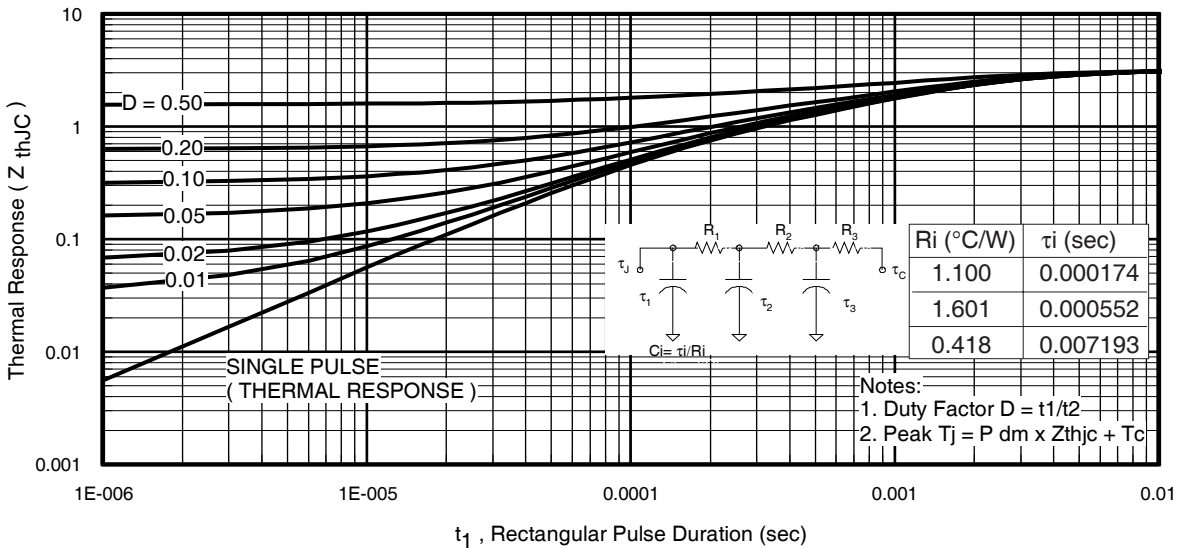


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

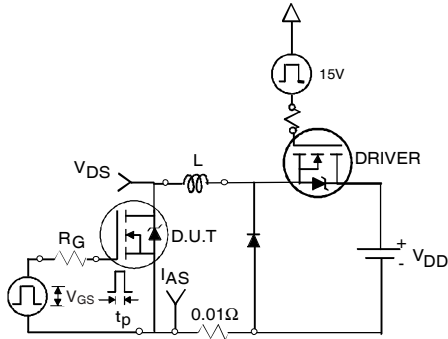


Fig 12a. Unclamped Inductive Test Circuit

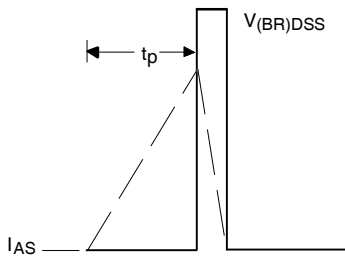


Fig 12b. Unclamped Inductive Waveforms

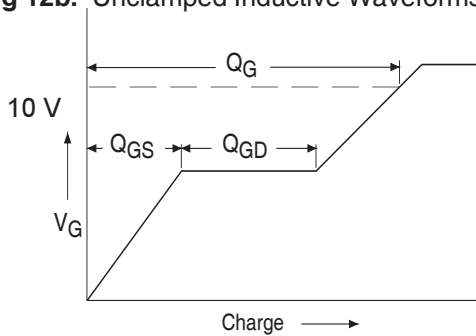


Fig 13a. Basic Gate Charge Waveform

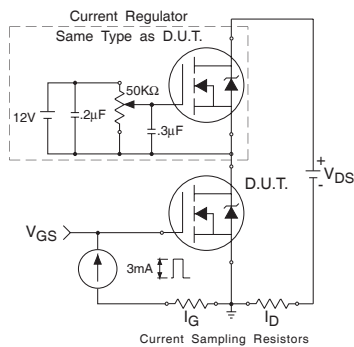


Fig 13b. Gate Charge Test Circuit
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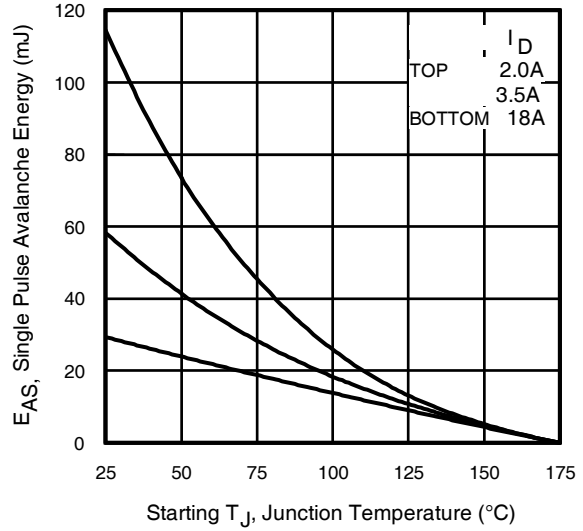


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

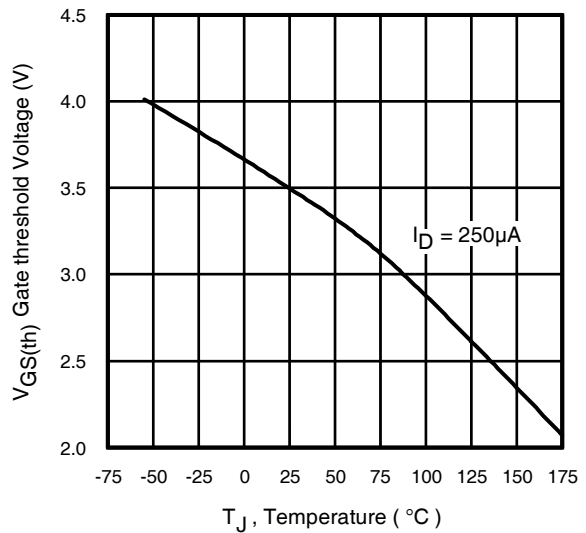


Fig 14. Threshold Voltage Vs. Temperature



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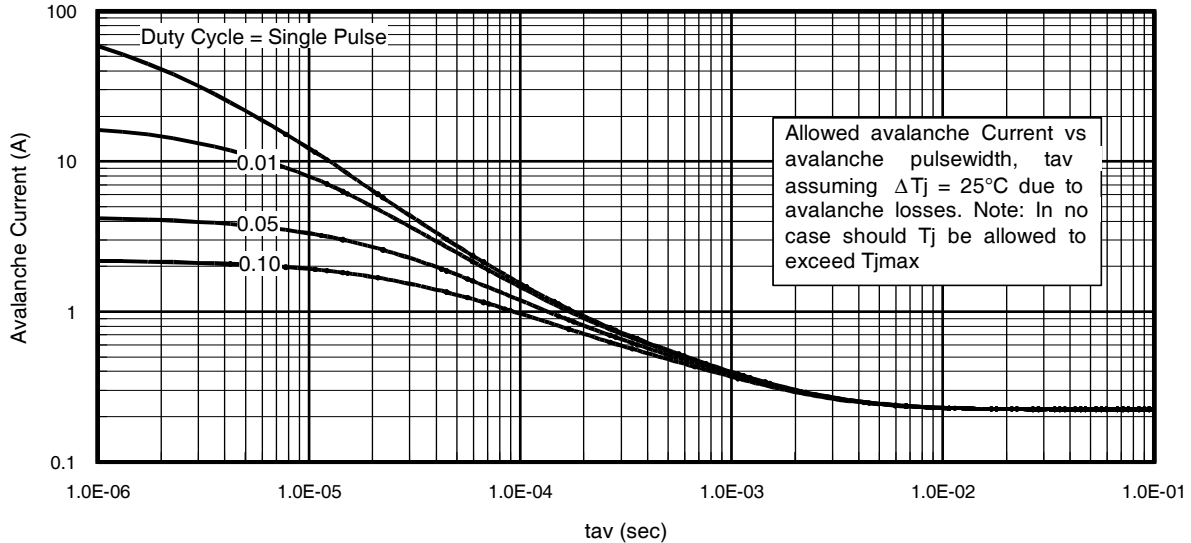


Fig 15. Typical Avalanche Current Vs.Pulsewidth

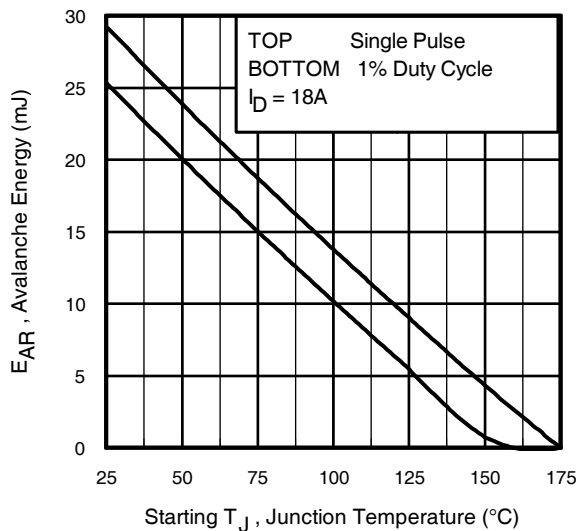


Fig 16. Maximum Avalanche Energy Vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

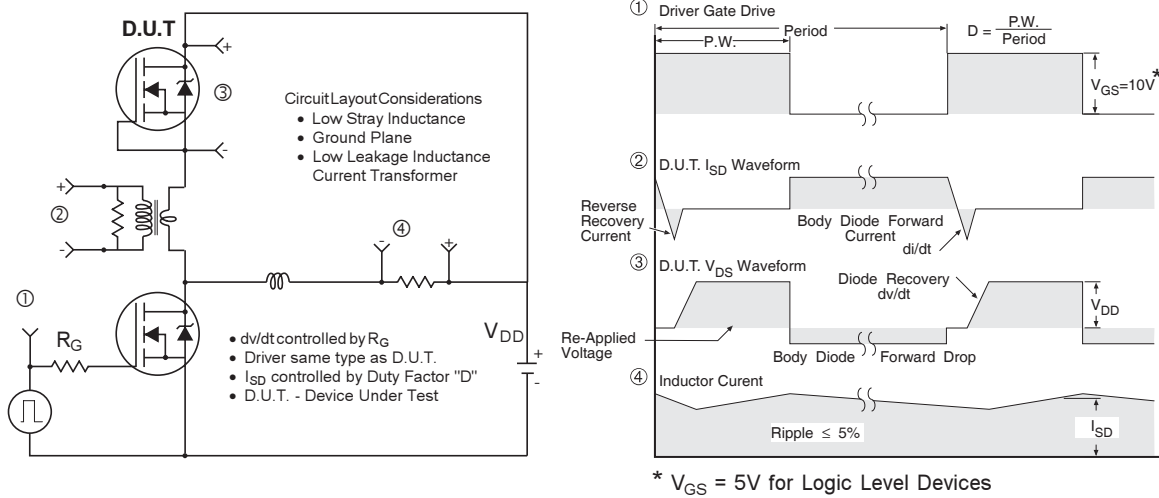


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

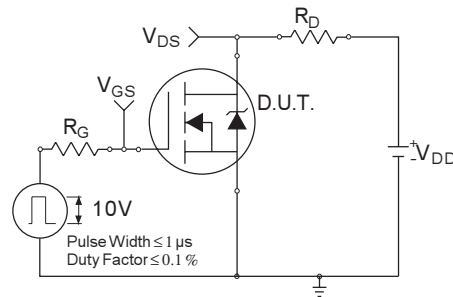


Fig 18a. Switching Time Test Circuit

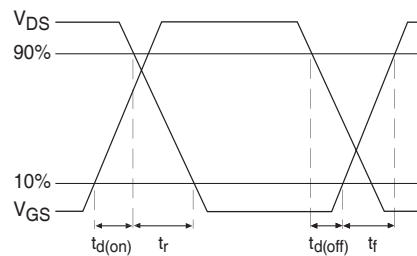
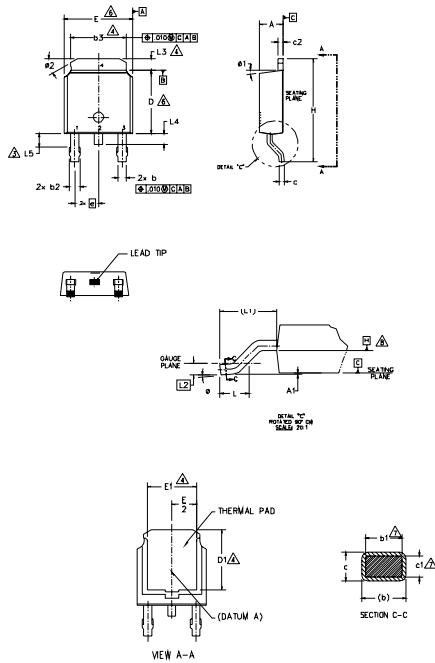


Fig 18b. Switching Time Waveforms

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D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2- DIMENSION ARE SHOWN IN INCHES (MILLIMETERS)
 - 3- LEAD DIMENSION UNCONTROLLED IN L.S.
 - 4- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD
 - 5- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP
 - 6- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

| SYMBOL | DIMENSIONS | | | | NOTES |
|----------|-------------|-------|-----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | .086 | .094 | |
| A1 | - | 0.13 | - | .005 | |
| b | 0.64 | 0.89 | .025 | .035 | |
| b1 | 0.65 | 0.79 | .025 | .031 | 7 |
| b2 | 0.76 | 1.14 | .030 | .046 | |
| b3 | 4.95 | 5.46 | .195 | .215 | 4 |
| c | 0.46 | 0.61 | .018 | .024 | |
| c1 | 0.41 | 0.56 | .016 | .022 | 7 |
| c2 | 0.46 | 0.89 | .018 | .035 | |
| D | 5.97 | 6.22 | .236 | .245 | 6 |
| D1 | 5.21 | - | .206 | - | 4 |
| E | 6.35 | 6.73 | .250 | .265 | 6 |
| E1 | 4.32 | - | .170 | - | 4 |
| e | 2.29 BSC | | .090 BSC | | |
| H | 9.40 | 10.41 | .370 | .410 | |
| L | 1.40 | 1.78 | .056 | .070 | |
| L1 | 2.74 BSC | | .108 REF. | | |
| L2 | 0.51 BSC | | .020 BSC | | |
| L3 | 0.89 | 1.27 | .035 | .050 | 4 |
| L4 | - | 1.02 | - | .040 | |
| L5 | 1.14 | 1.52 | .045 | .060 | 3 |
| ϕ | 0" | 10" | 0" | 10" | |
| $\phi 1$ | 0" | 15" | 0" | 15" | |
| $\phi 2$ | 25" | 35" | 25" | 35" | |

LEAD ASSIGNMENTS

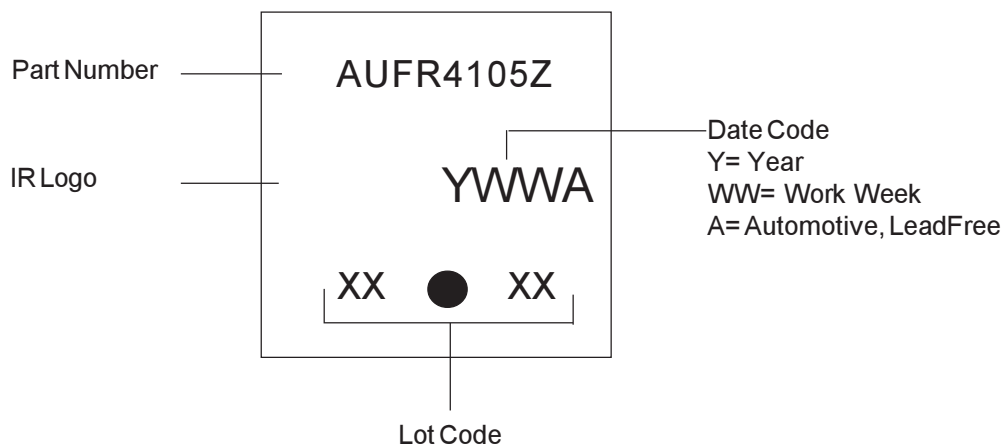
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

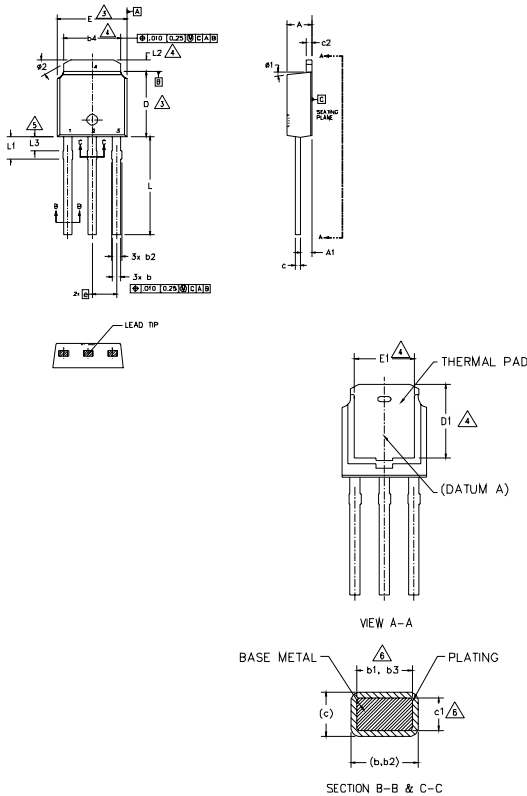
IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak Part Marking Information



I-Pak (TO-251AA) Package Outline



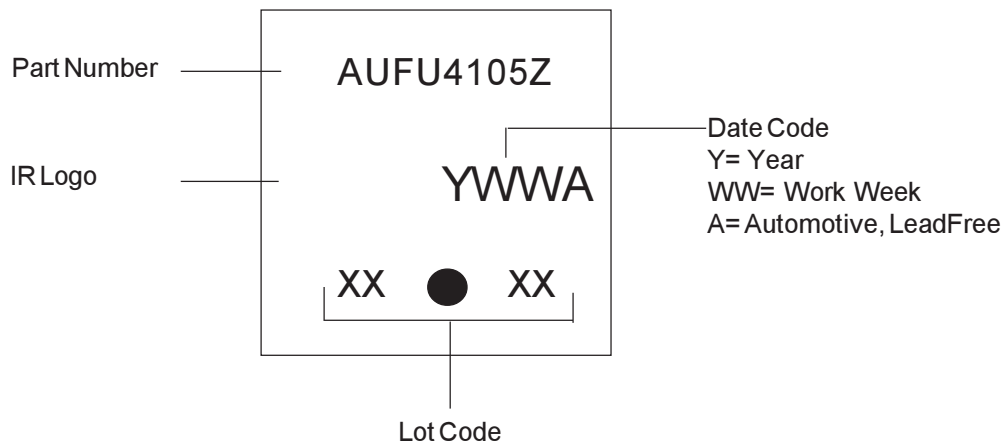
- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
 - 5.- LEAD DIMENSION UNCONTROLLED IN L3.
 - 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
 - 8.- CONTROLLING DIMENSION : INCHES.

| SYMBOL | DIMENSIONS | | | | NOTES |
|----------|-------------|------|--------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | .086 | .094 | |
| A1 | 0.89 | 1.14 | .035 | .045 | |
| b | 0.64 | 0.89 | .025 | .035 | |
| b1 | 0.65 | 0.79 | .025 | .031 | 6 |
| b2 | 0.76 | 1.14 | .030 | .045 | |
| b3 | 0.76 | 1.04 | .030 | .041 | 6 |
| b4 | 4.95 | 5.46 | .195 | .215 | 4 |
| c | 0.46 | 0.61 | .018 | .024 | |
| c1 | 0.41 | 0.56 | .016 | .022 | 6 |
| c2 | 0.46 | 0.89 | .018 | .035 | |
| D | 5.97 | 6.22 | .235 | .245 | 3 |
| D1 | 5.21 | - | .205 | - | 4 |
| E | 6.35 | 6.73 | .250 | .265 | 3 |
| E1 | 4.32 | - | .170 | - | 4 |
| e | 2.29 | BSC | .090 | BSC | |
| L | 8.89 | 9.65 | .350 | .380 | |
| L1 | 1.91 | 2.29 | .045 | .090 | |
| L2 | 0.89 | 1.27 | .035 | .050 | 4 |
| L3 | 1.14 | 1.52 | .045 | .060 | 5 |
| $\phi 1$ | 0" | 15" | 0" | 15" | |
| $\phi 2$ | 25" | 35" | 25" | 35" | |

LEAD ASSIGNMENTS

- HEXFET**
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

I-Pak Part Marking Information



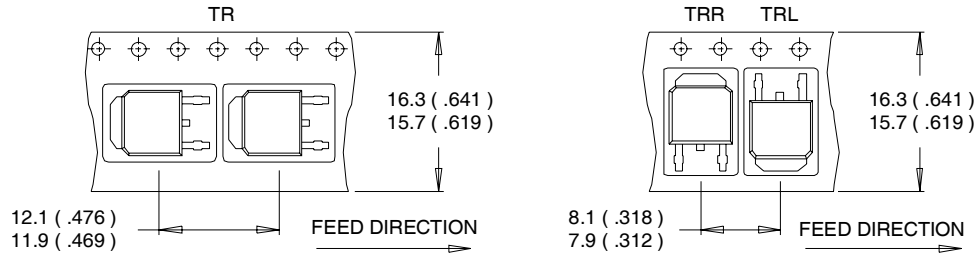


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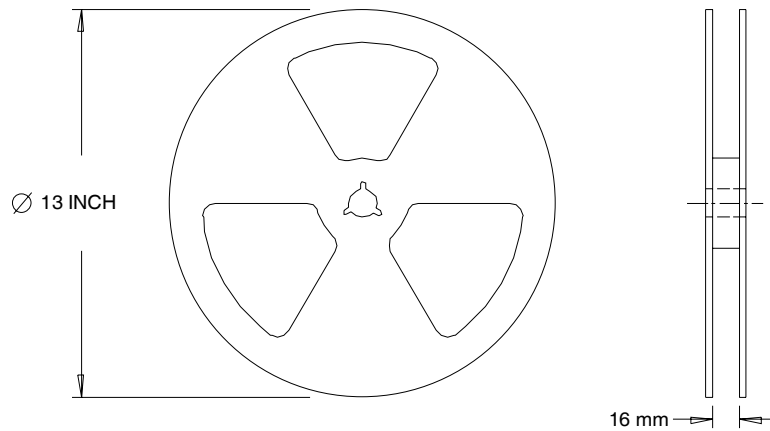
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} ; starting $T_J = 25^\circ C$, $L = 0.18mH$, $R_G = 25\Omega$, $I_{AS} = 18A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ③ Pulse width $\leq 1.0ms$; duty cycle $\leq 2\%$.
- ④ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population, starting $T_J = 25^\circ C$, $L = 0.18mH$, $R_G = 25\Omega$, $I_{AS} = 18A$, $V_{GS} = 10V$.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R_θ is measured at T_J approximately $90^\circ C$.